

SN74HCS266-Q1 Automotive Quadruple 2-Input XNOR Gates With Open-Drain Outputs and Schmitt-Trigger Inputs

1 Features

- AEC-Q100 Qualified for automotive applications:
 - Device temperature grade 1: -40°C to $+125^{\circ}\text{C}$, T_A
- Wide operating voltage range: 2V to 6V
- Schmitt-trigger inputs allow for slow or noisy input signals
- Low power consumption
 - Typical I_{CC} of 100nA
 - Typical input leakage current of $\pm 100\text{nA}$
- $\pm 7.8\text{mA}$ output drive at 6V

2 Applications

- [Detect phase differences in input signals](#)
- Create a selectable inverter or buffer

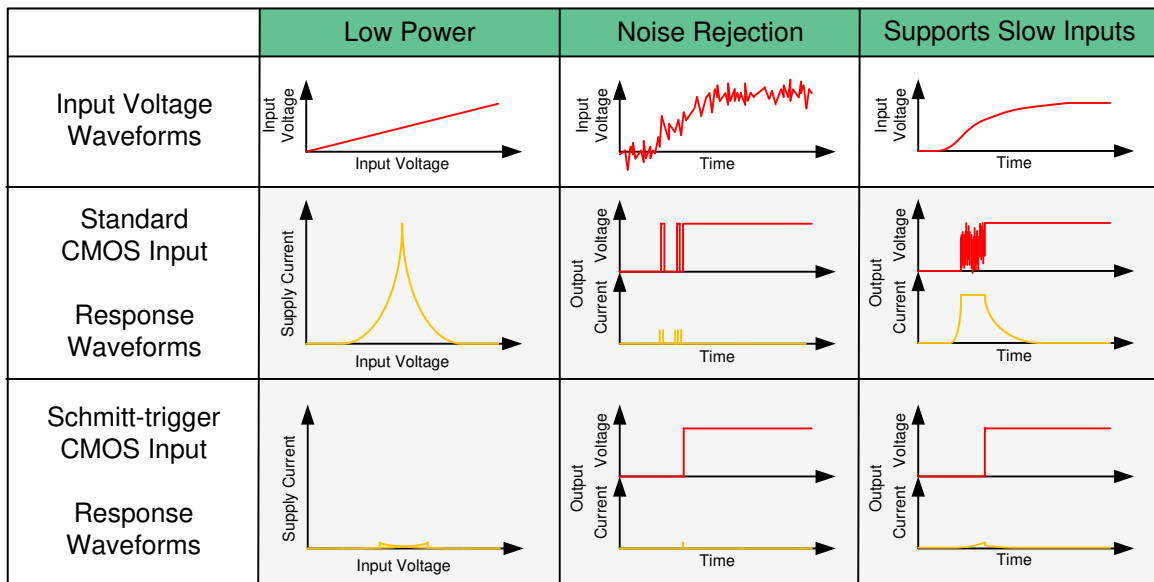
3 Description

This device contains four independent 2-input XNOR gates with open-drain outputs and Schmitt-trigger inputs. Each gate performs the Boolean function $Y = A \oplus B$ in positive logic.

Package Information

PART NUMBER	PACKAGE ⁽¹⁾	PACKAGE SIZE ⁽²⁾
SN74HCS266QPWR-Q1	PW (TSSOP, 14)	5.00mm × 4.40mm
SN74HCS266QDR-Q1	D (SOIC, 14)	8.70mm × 3.90mm

- (1) For all available packages, see the orderable addendum at the end of the data sheet.
- (2) The package size (length × width) is a nominal value and includes pins, where applicable.



Benefits of Schmitt-trigger Inputs



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4 Pin Configuration and Functions

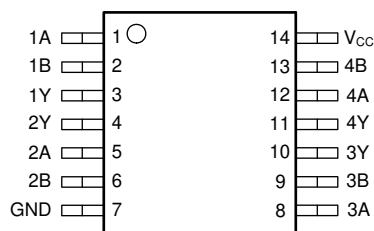


Figure 4-1. PW or D Package 14-Pin TSSOP or SOIC Top View

PIN		TYPE	DESCRIPTION
NAME	NO.		
1A	1	Input	Channel 1, Input A
1B	2	Input	Channel 1, Input B
1Y	3	Output	Channel 1, Output Y
2A	5	Input	Channel 2, Input A
2B	6	Input	Channel 2, Input B
2Y	4	Output	Channel 2, Output Y
3A	8	Input	Channel 3, Input A
3B	9	Input	Channel 3, Input B
3Y	10	Output	Channel 3, Output Y
4A	12	Input	Channel 4, Input A
4B	13	Input	Channel 4, Input B
4Y	11	Output	Channel 4, Output Y
GND	7	—	Ground
V _{CC}	14	—	Positive Supply

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V _{CC}	Supply voltage		–0.5	7	V
I _{IK}	Input clamp current ⁽²⁾	V _I < –0.5 V or V _I > V _{CC} + 0.5 V		±20	mA
I _{OK}	Output clamp current ⁽²⁾	V _I < –0.5 V or V _I > V _{CC} + 0.5 V		±20	mA
I _O	Continuous output current	V _O = 0 to V _{CC}		±35	mA
	Continuous current through V _{CC} or GND			±70	mA
T _J	Junction temperature ⁽³⁾			150	°C
T _{stg}	Storage temperature		–65	150	°C

(1) Operation outside the *Absolute Maximum Ratings* may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Conditions*. If briefly operating outside the *Recommended Operating Conditions* but within the *Absolute Maximum Ratings*, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.

(2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

(3) Verified by design.

5.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per AEC Q100-002 ⁽¹⁾ HBM ESD Classification Level 2	±4000	V
		Charged device model (CDM), per AEC Q100-011 CDM ESD Classification Level C6	±1500	

(1) AEC Q100-002 indicate that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V _{CC}	Supply voltage	2	5	6	V
V _I	Input voltage	0		V _{CC}	V
V _O	Output voltage	0		V _{CC}	V
T _A	Ambient temperature	–40		125	°C

5.4 Thermal Information

THERMAL METRIC ⁽¹⁾		SN74HCS266-Q1		UNIT
		PW (TSSOP)	D (SOIC)	
		14 PINS	14 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	151.7	133.6	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	79.4	89.0	°C/W
R _{θJB}	Junction-to-board thermal resistance	94.7	89.5	°C/W
Ψ _{JT}	Junction-to-top characterization parameter	25.2	45.5	°C/W
Ψ _{JB}	Junction-to-board characterization parameter	94.1	89.1	°C/W

THERMAL METRIC ⁽¹⁾		SN74HCS266-Q1		UNIT
		PW (TSSOP)	D (SOIC)	
		14 PINS	14 PINS	
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application note.

5.5 Electrical Characteristics

over operating free-air temperature range; typical ratings measured at $T_A = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP	MAX	UNIT
V_{T+}	Positive switching threshold			2V	1.18		1.3	V
				4.5V	2.39		2.58	
				6V	3.11		3.32	
V_{T-}	Negative switching threshold			2V	0.61		0.66	V
				4.5V	1.31		1.42	
				6V	1.72		1.87	
ΔV_T	$V_{T+} - V_{T-}$			2V	0.55		0.67	V
				4.5V	1.04		1.21	
				6V	1.34		1.49	
V_{OH}	High-level output voltage	$V_I = V_{IH}$ or V_{IL}	$I_{OH} = -20\mu\text{A}$	2V to 6V	$V_{CC} - 0.1$ $V_{CC} - 0.002$			V
			$I_{OH} = -6\text{mA}$	4.5V	4.0	4.3		
			$I_{OH} = -7.8\text{mA}$	6V	5.4	5.75		
V_{OL}	Low-level output voltage	$V_I = V_{IH}$ or V_{IL}	$I_{OL} = 20\mu\text{A}$	2V to 6V		0.002	0.1	V
			$I_{OL} = 4\text{mA}$	4.5V		0.18	0.30	
			$I_{OL} = 7.8\text{mA}$	6V		0.22	0.33	
I_I	Input leakage current	$V_I = V_{CC}$ or 0		6V		± 100	± 1000	nA
I_{CC}	Supply current	$V_I = V_{CC}$ or 0, $I_O = 0$		6V		0.1	2	μA
C_i	Input capacitance			2V to 6V			5	pF
C_{pd}	Power dissipation capacitance per gate	No load		2V to 6V		10		pF

5.6 Switching Characteristics

$C_L = 50\text{ pF}$; over operating free-air temperature range; typical values measured at $T_A = 25^\circ\text{C}$ (unless otherwise noted). See [Parameter Measurement Information](#).

PARAMETER		FROM (INPUT)	TO (OUTPUT)	V_{CC}	MIN	TYP	MAX	UNIT
t_{pd}	Propagation delay	A or B	Y	2 V		14	40	ns
				4.5 V		6	17	
				6 V		5	16	
t_t	Transition-time		Y	2 V		9	16	ns
				4.5 V		5	9	
				6 V		4	8	

5.7 Typical Characteristics

$T_A = 25^\circ\text{C}$

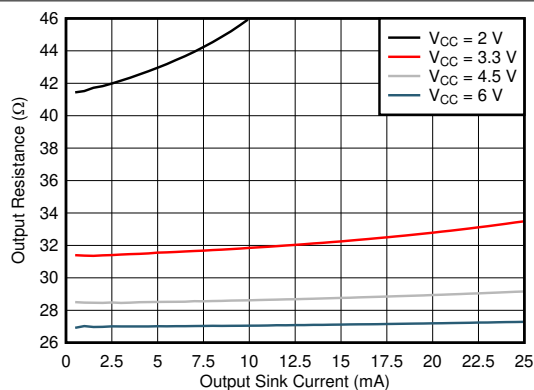


Figure 5-1. Output Driver Resistance in Low State

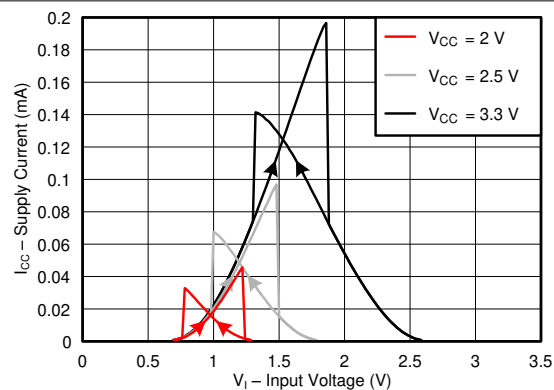


Figure 5-2. Typical Supply Current Versus Input Voltage Across Common Supply Values (2V to 3.3V)

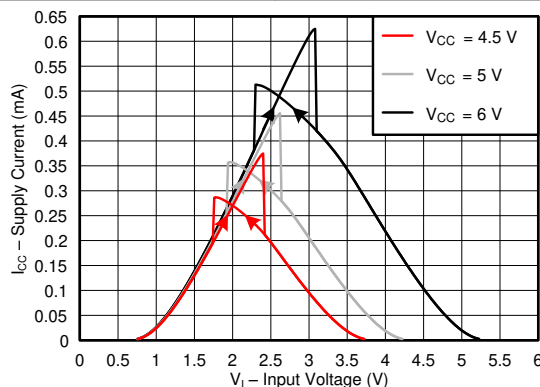
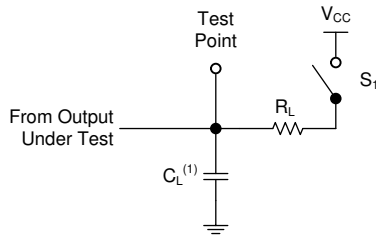


Figure 5-3. Typical Supply Current Versus Input Voltage Across Common Supply Values (4.5V to 6V)

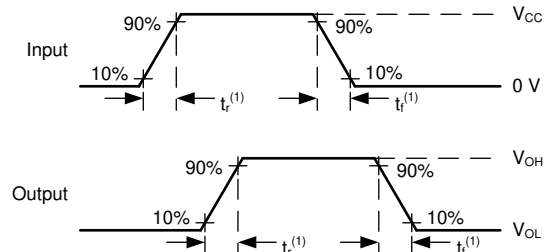
6 Parameter Measurement Information

- Phase relationships between waveforms are chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: $PRR \leq 1\text{MHz}$, $Z_O = 50\Omega$, $t_f < 6\text{ns}$.
- The outputs are measured one at a time, with one input transition per measurement.



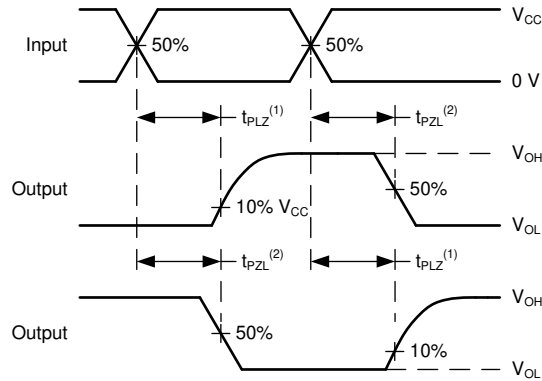
A. $C_L = 50\text{pF}$ and includes probe and jig capacitance.

Figure 6-1. Load Circuit



A. The maximum between t_r and t_f is used for t_t .

Figure 6-2. Voltage Waveforms Transition Times



A. The maximum between t_{PLH} and t_{PHL} is used for t_{pd} .

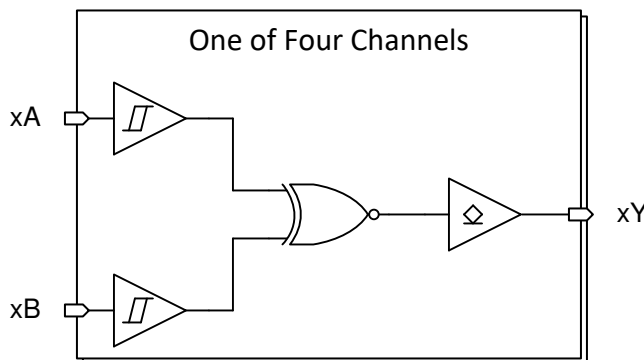
Figure 6-3. Voltage Waveforms Propagation Delays

7 Detailed Description

7.1 Overview

This device contains four independent 2-input XNOR gates with open-drain outputs and Schmitt-trigger inputs. Each gate performs the Boolean function $Y = \overline{A \oplus B}$ in positive logic.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Open-Drain CMOS Outputs

This device includes open-drain CMOS outputs. Open-drain outputs can only drive the output low. When in the high logical state, open-drain outputs are in a high-impedance state. The drive capability of this device can create fast edges into light loads, so consider routing and load conditions to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. Limit the device output power to avoid damage due to overcurrent. Follow the electrical and thermal limits defined in the *Absolute Maximum Ratings* at all times.

When placed into the high-impedance state, the output neither sources nor sinks current, with the exception of minor leakage current as defined in the *Electrical Characteristics* table. In the high-impedance state, the output voltage is not controlled by the device and is dependent on external factors. If no other drivers are connected to the node, then this is known as a floating node and the voltage is unknown. A pullup resistor can be connected to the output to provide a known voltage at the output while the output is in the high-impedance state. The value of the resistor depends on multiple factors, including parasitic capacitance and power consumption limitations. Typically, use a 10kΩ resistor to meet these requirements.

Leave unused open-drain CMOS outputs disconnected.

7.3.2 CMOS Schmitt-Trigger Inputs

Standard CMOS inputs are high impedance and are typically modeled as a resistor from the input to ground in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using Ohm's law ($R = V \div I$).

The Schmitt-trigger input architecture provides hysteresis as defined by ΔV_T in the *Electrical Characteristics*, which makes this device extremely tolerant to slow or noisy inputs. While the inputs can be driven much slower than standard CMOS inputs, properly terminating unused inputs is recommended. Driving the inputs slowly also increases dynamic current consumption of the device. For additional information regarding Schmitt-trigger inputs, please see [Understanding Schmitt Triggers](#).

7.3.3 Clamp Diode Structure

The inputs and outputs to this device have both positive and negative clamping diodes as depicted in [Figure 7-1](#).

CAUTION

Voltages beyond the values specified in the Absolute Maximum Ratings table can cause damage to the device. The recommended input and output voltage ratings can be exceeded if the input and output clamp-current ratings are observed.

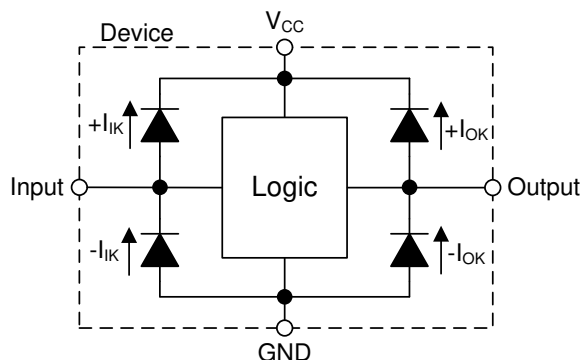


Figure 7-1. Electrical Placement of Clamping Diodes for Each Input and Output

7.4 Device Functional Modes

Table 7-1. Function Table

INPUTS		OUTPUT
A	B	Y
L	L	Z
L	H	L
H	L	L
H	H	Z

8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

In this application, an open-drain XNOR is used to control a clock source polarity. A Low on the control input inverts the signal. The Schmitt-trigger inputs help to mitigate noise on the clock signal and allows for additional filtering.

8.2 Typical Application

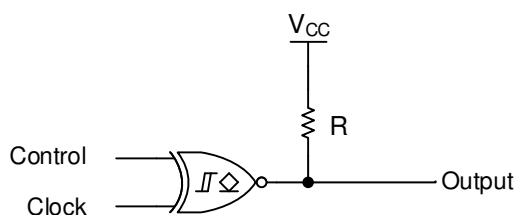


Figure 8-1. Typical application block diagram

8.2.1 Design Requirements

8.2.1.1 Power Considerations

Verify that the desired supply voltage is within the range specified in the [Recommended Operating Conditions](#). The supply voltage sets the electrical characteristics of the device as described in the [Electrical Characteristics](#).

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74HCS266-Q1 plus the maximum supply current, I_{CC} , listed in [Electrical Characteristics](#). The logic device can only sink as much current as is provided by the external pull-up resistor or other supply source. Do not exceed the maximum total current through GND listed in the [Absolute Maximum Ratings](#).

Total power consumption can be calculated using the information provided in [CMOS Power Consumption and \$C_{pd}\$ Calculation](#).

Thermal increase can be calculated using the information provided in [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices](#).

CAUTION

The maximum junction temperature, $T_J(\text{max})$ listed in the [Absolute Maximum Ratings](#), is an *additional limitation* to prevent damage to the device. Do not violate any values listed in the [Absolute Maximum Ratings](#). These limits are provided to prevent damage to the device.

8.2.1.2 Input Considerations

Input signals must cross $V_L(\text{min})$ to be considered a logic LOW, and $V_{th}(\text{max})$ to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the [Absolute Maximum Ratings](#).

Unused inputs must be terminated to either V_{CC} or ground. These can be directly terminated if the input is completely unused, or the input can be connected with a pullup or pulldown resistor if the input is to be used sometimes, but not always. A pullup resistor is used for a default state of HIGH, and a pulldown resistor is used for a default state of LOW. The resistor size is limited by drive current of the controller, leakage current into the

SN74HCS266-Q1, as specified in the [Section 5.5](#), and the desired input transition rate. A 10k Ω resistor value is often used due to these factors.

The SN74HCS266-Q1 has no input signal transition rate requirements because device has Schmitt-trigger inputs.

Another benefit to having Schmitt-trigger inputs is the ability to reject noise. Noise with a large enough amplitude can still cause issues. To know how much noise is too much, please refer to the $\Delta V_T(\text{min})$ in the [Section 5.5](#). This hysteresis value provides the peak-to-peak limit.

Unlike what happens with standard CMOS inputs, Schmitt-trigger inputs can be held at any valid value without causing huge increases in power consumption. The typical additional current caused by holding an input at a value other than V_{CC} or ground is plotted in the [Typical Characteristics](#).

Refer to the [Feature Description](#) for additional information regarding the inputs for this device.

8.2.1.3 Output Considerations

The ground voltage is used to produce the output LOW voltage. Sinking current into the output increases the output voltage as specified by the V_{OL} specification in the [Electrical Characteristics](#). The plot in [Section 5.7](#) provides a typical relationship between output voltage and current for this device.

Open-drain outputs can be directly connected together to produce a wired-AND. This is possible because the outputs cannot source current, and thus can never be in bus-contention.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to [Feature Description](#) for additional information regarding the outputs for this device.

8.2.2 Detailed Design Procedure

1. Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the [Section 8.4](#).
2. Verify that the capacitive load at the output is $\leq 70\text{pF}$. This is not a hard limit, however this limit verifies optimal performance. This can be accomplished by providing short, appropriately sized traces from the SN74HCS266 SN74HCS266-Q1 to the receiving device.
3. Verify that the resistive load at the output is larger than $(V_{CC} / I_O(\text{max})) \Omega$. This verifies that the maximum output current from the *Absolute Maximum Ratings* is not violated. Most CMOS inputs have a resistive load measured in M Ω ; much larger than the minimum calculated above.
4. Thermal issues are rarely a concern for logic gates, however the power consumption and thermal increase can be calculated using the steps provided in the application note, [CMOS Power Consumption and Cpd Calculation](#)

8.2.3 Application Curves

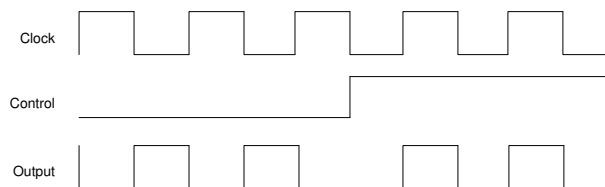


Figure 8-2. Application timing diagram

8.3 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the [Recommended Operating Conditions](#). Each V_{CC} terminal must have a bypass capacitor to prevent power disturbance. A 0.1 μF capacitor is recommended for this device. Multiple bypass capacitors can be placed in parallel to reject different frequencies of noise. The 0.1 μF and 1 μF capacitors are commonly used in parallel.

The bypass capacitor must be installed as close to the power terminal as possible for best results, as shown in [Figure 8-3](#).

8.4 Layout

8.4.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC} , whichever makes more sense for the logic function or is more convenient.

8.4.2 Layout Example

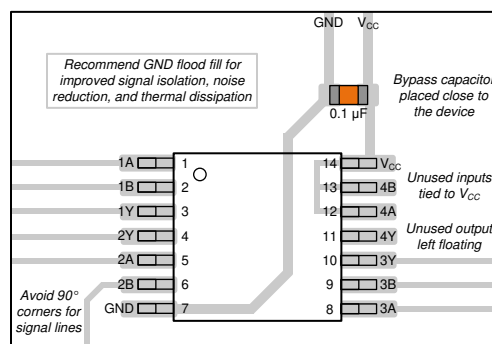


Figure 8-3. Example Layout for the SN74HCS266-Q1

9 Device and Documentation Support

9.1 Documentation Support

9.1.1 Related Documentation

For related documentation see the following:

- [Reduce Noise and Save Power with the New HCS Logic Family](#)
- [CMOS Power Consumption and CPD Calculation](#)
- [Designing with Logic](#)

9.2 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

9.3 Support Resources

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

9.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.6 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from October 15, 2020 to March 13, 2026 (from Revision A (October 2020) to Revision B (March 2026))

	Page
• Updated the numbering format for tables, figures and cross-references throughout the document.....	1
• Changed V_{T+} limits at 2V V_{CC} from 0.7V (min), 1.5V (max) to 1.18V (min), 1.3V (max)	5
• Changed V_{T+} limits at 4.5V V_{CC} from 1.7V (min), 3.15V (max) to 2.39V (min), 2.58V (max)	5
• Changed V_{T+} limits at 6V V_{CC} from 2.1V (min), 4.2V (max) to 3.11V (min), 3.32V (max)	5
• Changed V_{T-} limits at 2V V_{CC} from 0.3V (min), 1.0V (max) to 0.61V (min), 0.66V (max).....	5
• Changed V_{T-} limits at 4.5V V_{CC} from 0.9V (min), 2.2V (max) to 1.31V (min), 1.42V (max)	5
• Changed V_{T-} limits at 6V V_{CC} from 1.2V (min), 3.0V (max) to 1.72V (min), 1.87V (max).....	5
• Changed ΔV_T limits at 2V V_{CC} from 0.2V (min), 1.0V (max) to 0.55V (min), 0.67V (max).....	5
• Changed ΔV_T limits at 4.5V V_{CC} from 0.4V (min), 1.4V (max) to 1.04V (min), 1.21V (max).....	5
• Changed ΔV_T limits at 6V V_{CC} from 0.6V (min), 1.6V (max) to 1.34V (min), 1.49V (max).....	5
• Improved clarity of functionality for the device.....	8

Changes from June 24, 2020 to October 15, 2020 (from Revision * (June 2020) to Revision A (October 2020))**Page**

- Updated the numbering format for tables, figures and cross-references throughout the document..... 1
- Improved clarity of functionality for the device.....8

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
SN74HCS266QDRQ1	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HC266Q1
SN74HCS266QDRQ1.A	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HC266Q1
SN74HCS266QPWRQ1	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	HC266Q1
SN74HCS266QPWRQ1.A	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HC266Q1

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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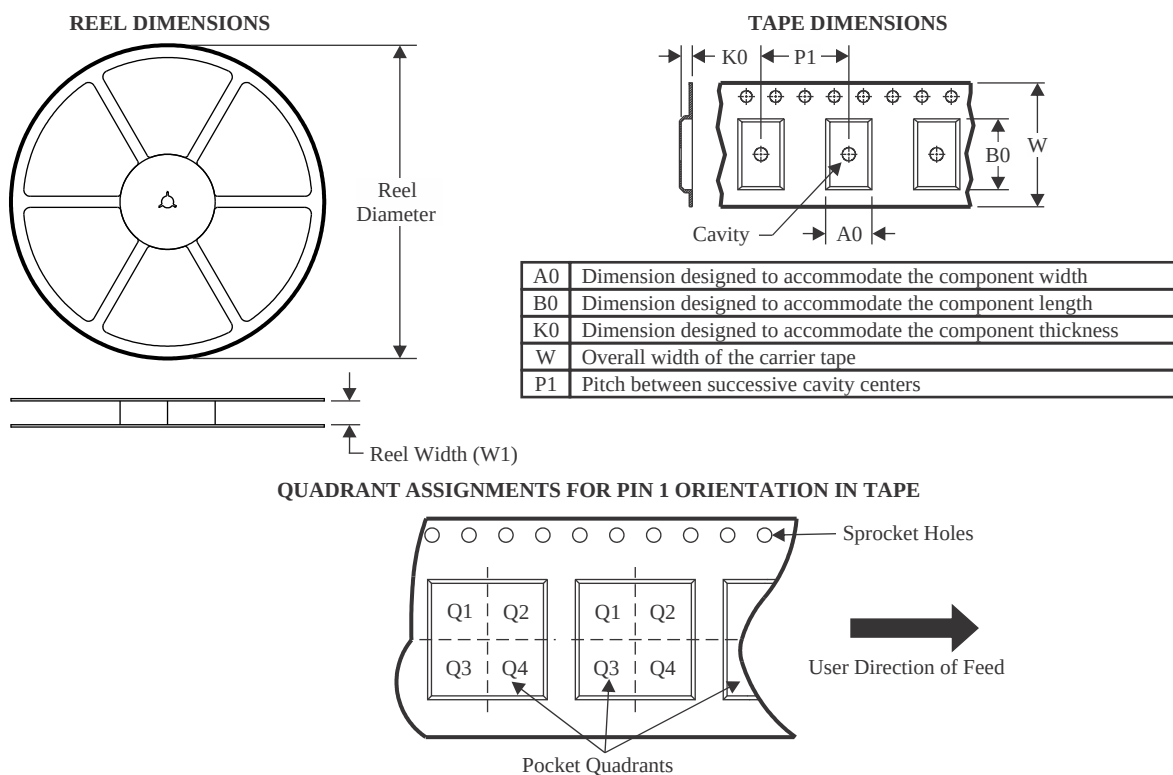
OTHER QUALIFIED VERSIONS OF SN74HCS266-Q1 :

- Catalog : [SN74HCS266](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product

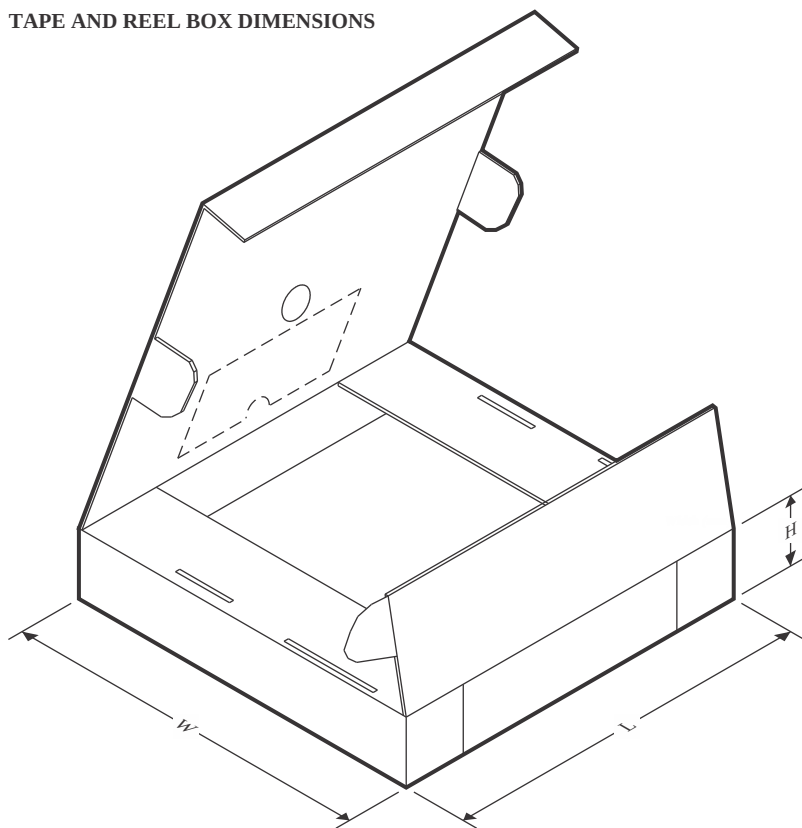
TAPE AND REEL INFORMATION



*All dimensions are nominal

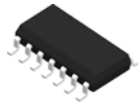
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74HCS266QDRQ1	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74HCS266QPWRQ1	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS

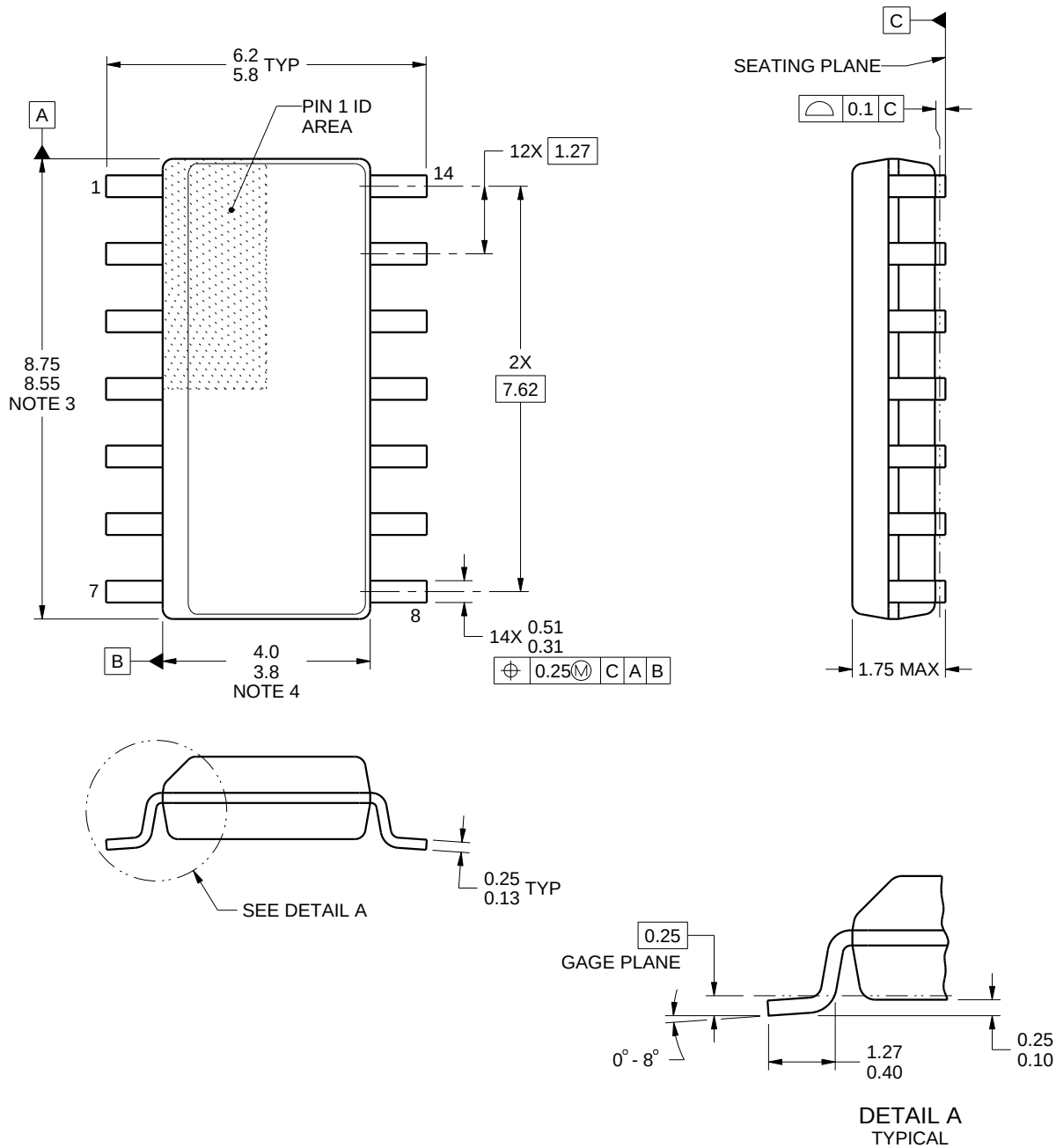


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74HCS266QDRQ1	SOIC	D	14	2500	353.0	353.0	32.0
SN74HCS266QPWRQ1	TSSOP	PW	14	2000	356.0	356.0	35.0

D0014A**PACKAGE OUTLINE****SOIC - 1.75 mm max height**

SMALL OUTLINE INTEGRATED CIRCUIT



4220718/A 09/2016

NOTES:

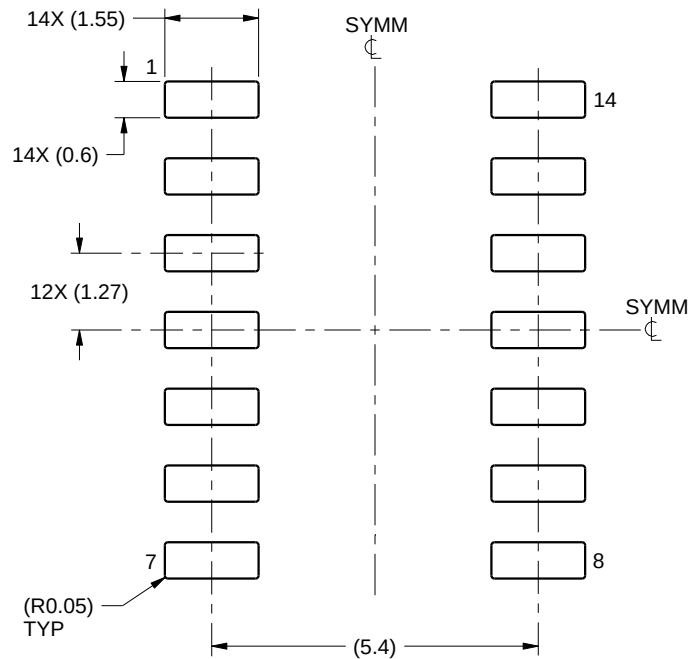
1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm, per side.
5. Reference JEDEC registration MS-012, variation AB.

EXAMPLE BOARD LAYOUT

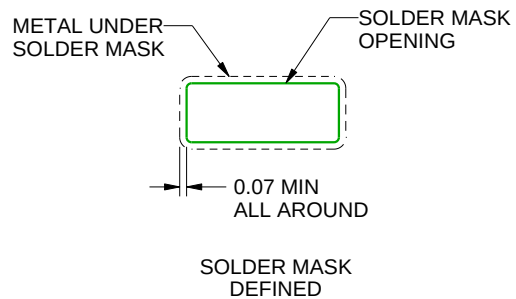
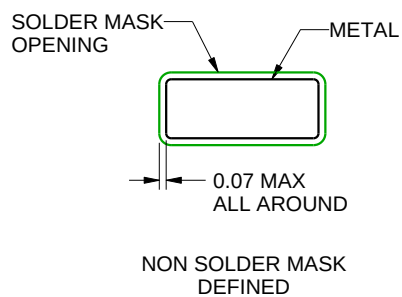
D0014A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE
SCALE:8X



SOLDER MASK DETAILS

4220718/A 09/2016

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

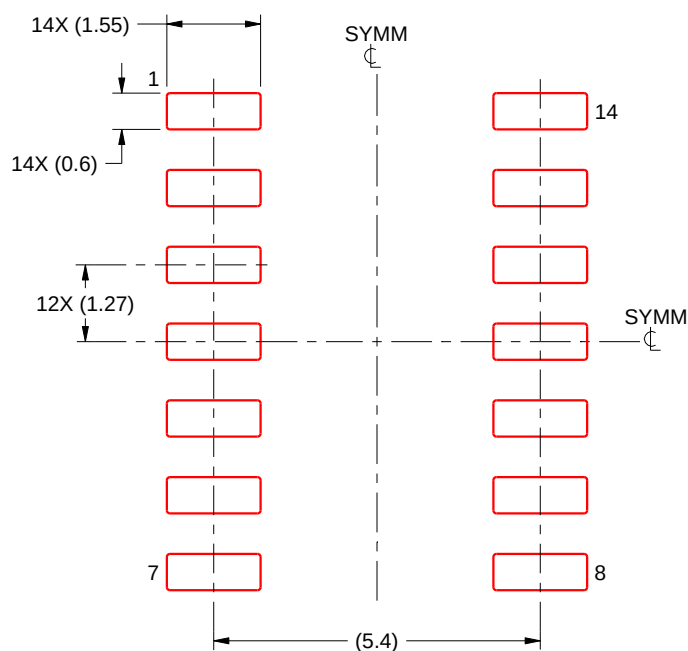
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0014A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:8X

4220718/A 09/2016

NOTES: (continued)

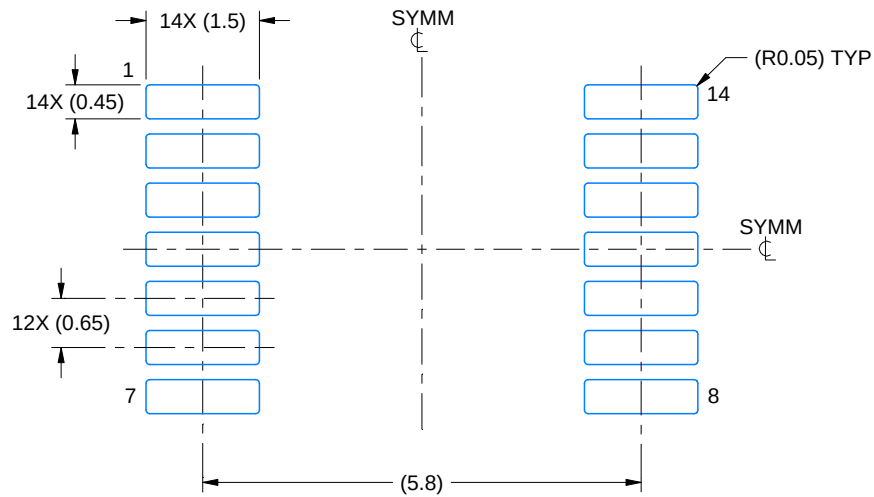
8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

EXAMPLE BOARD LAYOUT

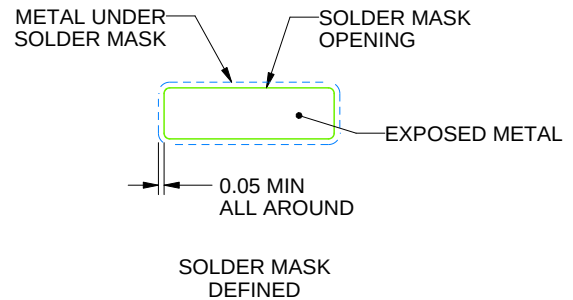
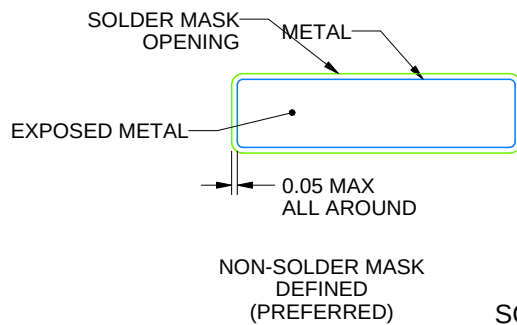
PW0014A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



SOLDER MASK DETAILS

4220202/B 12/2023

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

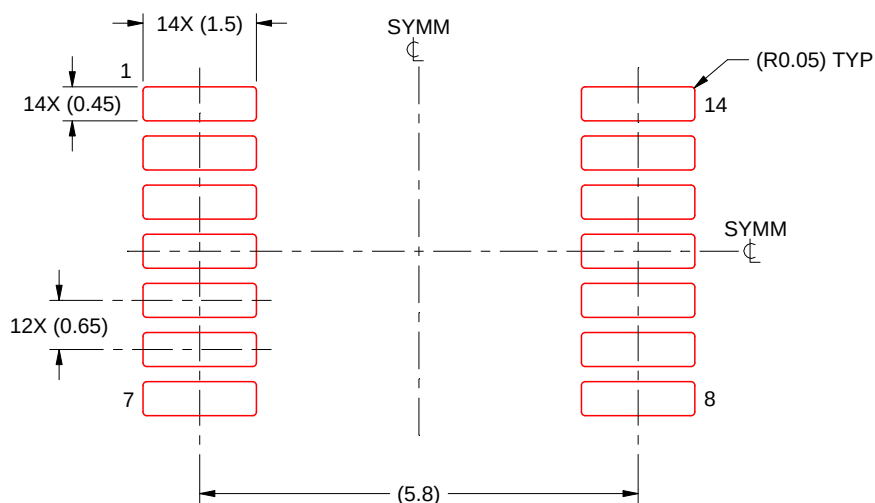
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

PW0014A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220202/B 12/2023

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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